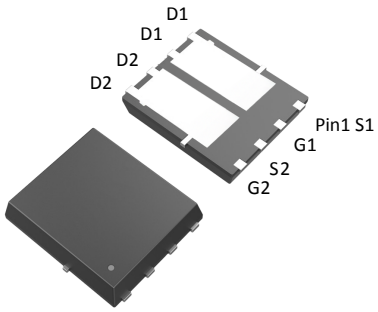
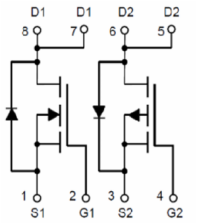
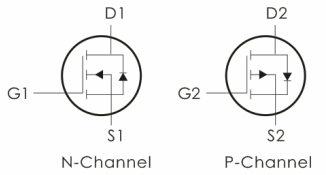
Description：

This N+P Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.







Features：

N-Channel:V_{DS}=40V,I_D=24A,$R_{DS(ON)}$<17mΩ @V_{GS}=10V（Typ：14mΩ）

P-Channel: V_{DS}=-40V,I_D=-24 A,$R_{DS(ON)}$<28mΩ @V_{GS}=-10V（Typ：22mΩ）

1) Low gate charge.
2) Green device available.
3) Advanced high cell denity trench technology for ultra low $R_{DS(ON)}$.
4) Excellent package for good heat dissipation.
5) MSL3

Package Marking and Ordering Information：

Part NO.	Marking	Package	Packing
DON619C	N619C	DFN5*6-8D	5000 pcs/Reel

Absolute Maximum Ratings： (T_C=25℃ unless otherwise noted)

Symbol	Parameter	N-Channel	P-Channel	Units
V_{DS}	Drain-Source Voltage	40	-40	V
V_{GS}	Gate-Source Voltage	±20	±20	V
I_D	Continuous Drain Current- T_C=25℃ [1]	24	-24	A
	Continuous Drain Current-T_C=100℃ [1]	16.8	-16.8	
I_{DM}	Pulsed Drain Current [2]	96	-96	A
E_{AS}	Single pulse avalanche energy [3]	10.8	22	mJ
P_D	Power Dissipation - T_C=25℃	18	21	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150		℃

Thermal Characteristics：

Symbol	Parameter	N-CH	P-CH	Units
$R_{\theta JC}$	Thermal Resistance,Junction to Cast	7	6	℃/W

N-Channel Electrical Characteristics: (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Sourtce Breakdown Voltage	V_{GS}=0V,I_D=250μA	40	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS}=0V, V_{DS}=40V	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V, V_{DS}=0A	---	---	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate-Source Threshold Voltage	V_{GS}=V_{DS}, I_D=250μA	1	1.6	2.5	V
$R_{DS(ON)}$	Drain-Source On Resistance[4]	V_{GS}=10V,I_D=4A	---	14	17	mΩ
		V_{GS}=4.5V,I_D=3A	---	18	28	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=20V, V_{GS}=0V, f=1MHz	---	1000	---	pF
C_{oss}	Output Capacitance		---	96	---	
C_{rss}	Reverse Transfer Capacitance		---	67.5	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DS}=20V, I_D=5A, R_{ENG}=6Ω ,V_{GS}=10V	---	10	---	ns
t_r	Rise Time		---	12	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	35	---	ns
t_f	Fall Time		---	8	---	ns
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=20V, I_D=5A	---	20	---	nC
Q_{gs}	Gate-Source Charge		---	1.8	---	nC
Q_{gd}	Gate-Drain “Miller” Charge		---	2.2	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	V_{GS}=0V, I_{SD}=8A	---	---	1.2	V
I_S	Continuous Drain Curren	V_D=V_G=0V	---	---	20	A
I_{SM}	Pulsed Drain Current		---	---	80	A

Notes:

1. Computed continuous current assumes the condition of $T_{j,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. EAS condition : TJ=25℃,VDD=20V,V_G=10V,L=0.1mH
4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

N-Typical Characteristics： (T_C=25℃ unless otherwise noted)

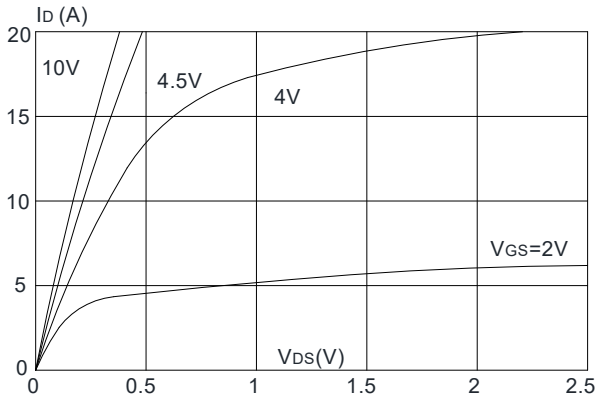


Figure1: Output Characteristics

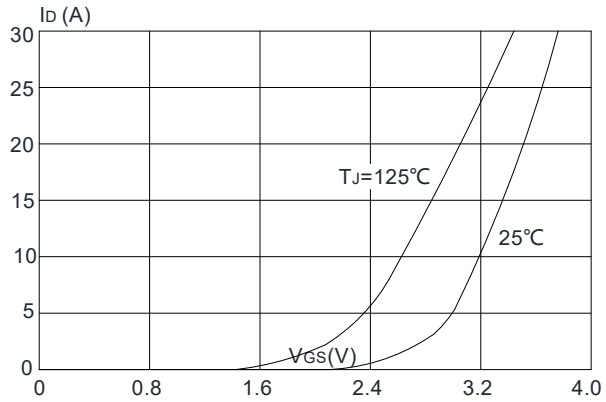


Figure 2: Typical Transfer Characteristics

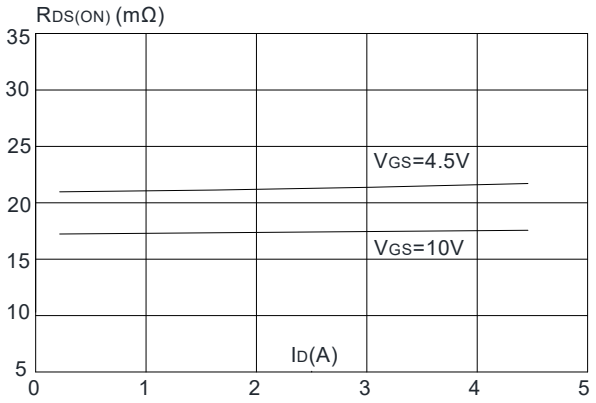


Figure 3: On-resistance vs. Drain Current

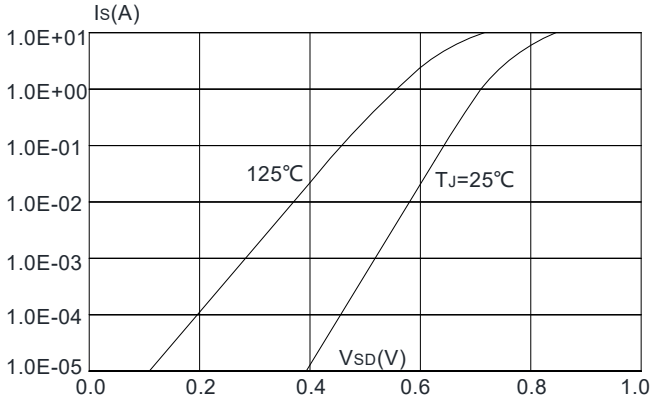


Figure 4: Body Diode Characteristics

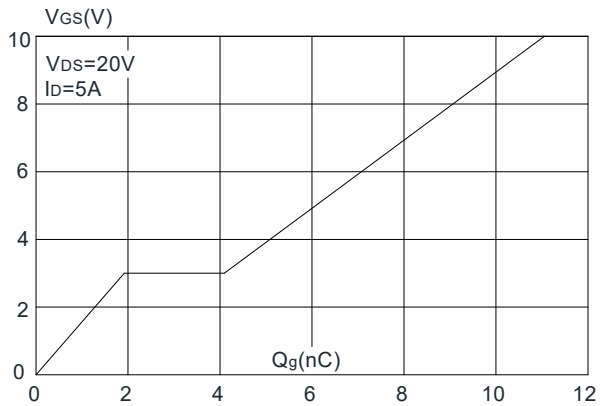


Figure 5: Gate Charge Characteristics

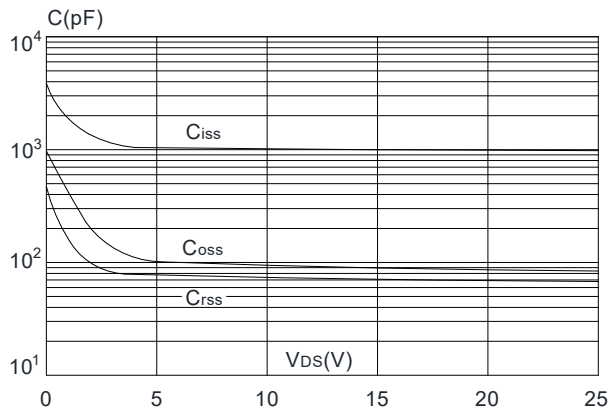


Figure 6: Capacitance Characteristics

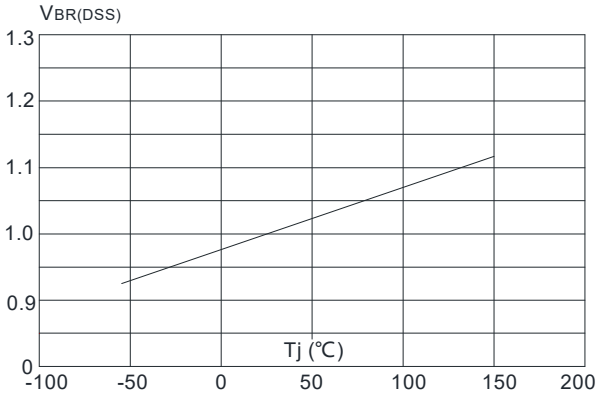


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

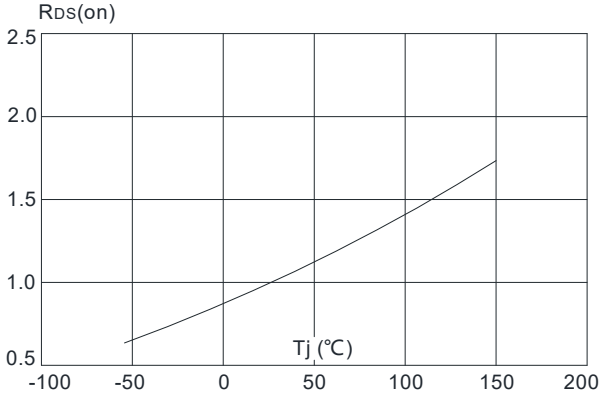


Figure 8: Normalized on Resistance vs. Junction Temperature

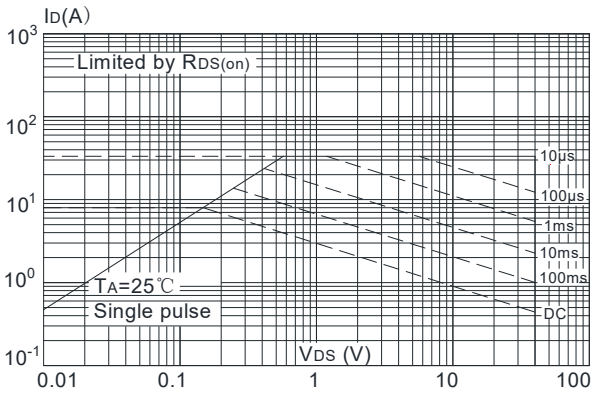


Figure 9: Maximum Safe Operating Area

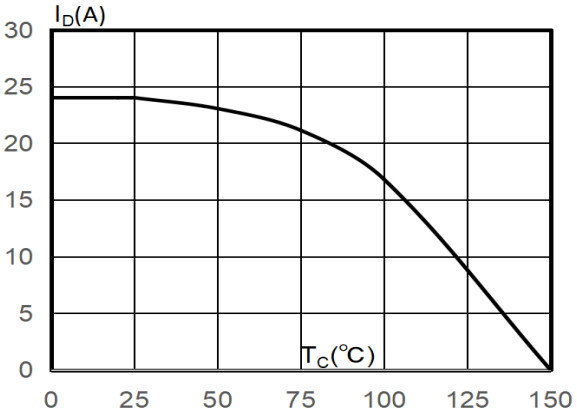


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

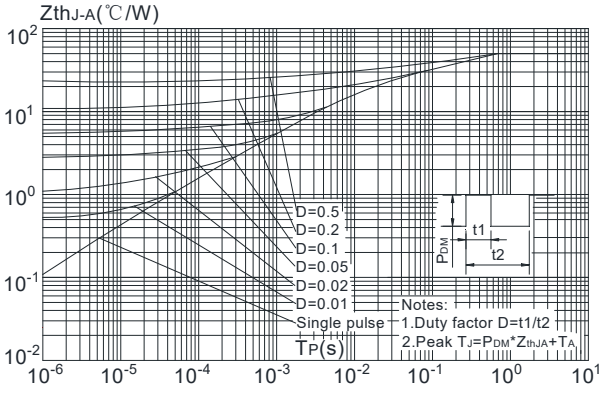


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

P-Channel Electrical Characteristics: (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Sourtce Breakdown Voltage	V_{GS}=0V,I_D=250μA	-40	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS}=0V, V_{DS}=-40V	---	---	-1	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V, V_{DS}=0A	---	---	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate-Source Threshold Voltage	V_{GS}=V_{DS}, I_D=250μA	-1	-1.6	-2.5	V
$R_{DS(ON)}$	Drain-Source On Resistance[4]	V_{GS}=-10V,I_D=-5A	---	22	28	mΩ
		V_{GS}=-4.5V,I_D=-5A	---	26	34	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=-20V, V_{GS}=0V, f=1MHz	---	1500	---	pF
C_{oss}	Output Capacitance		---	173	---	
C_{rss}	Reverse Transfer Capacitance		---	147	---	
Switching Characteristics[4]						
$t_{d(on)}$	Turn-On Delay Time	V_{DD}= -20V,I_D=-20A V_{GS}= -10V, R_{GEN}=3Ω	---	8	---	ns
t_r	Rise Time		---	7	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	25	---	ns
t_f	Fall Time		---	9	---	ns
Q_g	Total Gate Charge	V_{GS}=-10V,V_{DS}=-20V, I_D=-5A	---	30	---	nC
Q_{gs}	Gate-Source Charge		---	3.1	---	nC
Q_{gd}	Gate-Drain “Miller” Charge		---	5	---	nC
Drain-Source Diode Characteristics						
I_S	Continuous Drain to Source Diode	VD=VG=0V	---	---	-20	A
I_{SM}	Pulsed Drain to Source Diode		---	---	-80	---
V_{SD}	Source-Drain Diode Forward Voltage	V_{GS}=0V,I_S=-6A	---	---	-1.2	V

Notes:

1. Computed continuous current assumes the condition of $T_{j,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. EAS condition : TJ=25℃,VDD=-20V,V_G=-10V,L=0.1mH
4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

P-Typical Characteristics: (T_C=25℃ unless otherwise noted)

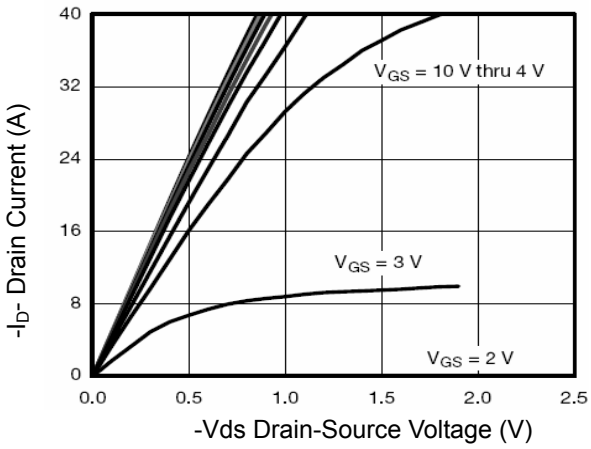


Figure 1 Output Characteristics

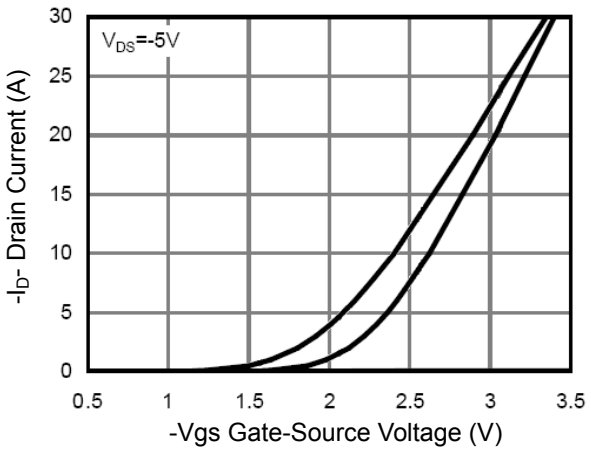


Figure 2 Transfer Characteristics

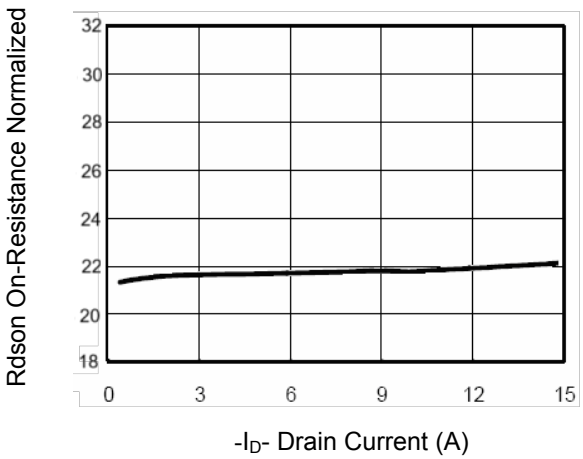


Figure 3 Rdson- Drain Current

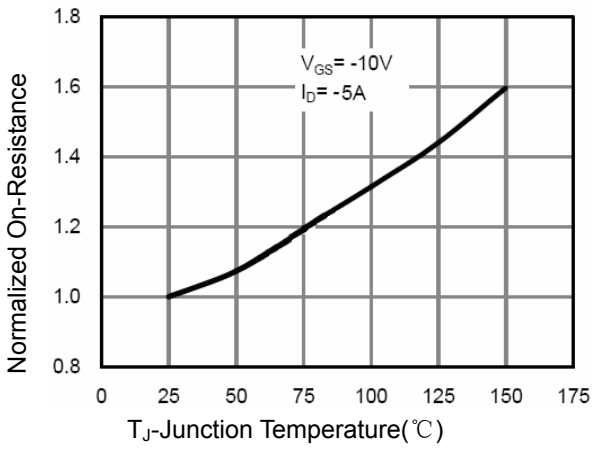


Figure 4 Rdson-Junction Temperature

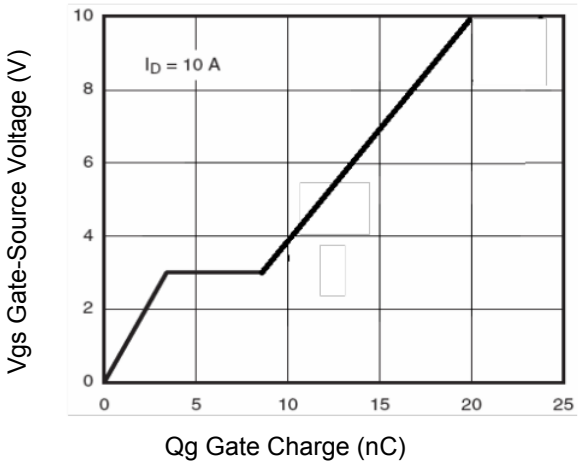


Figure 5 Gate Charge

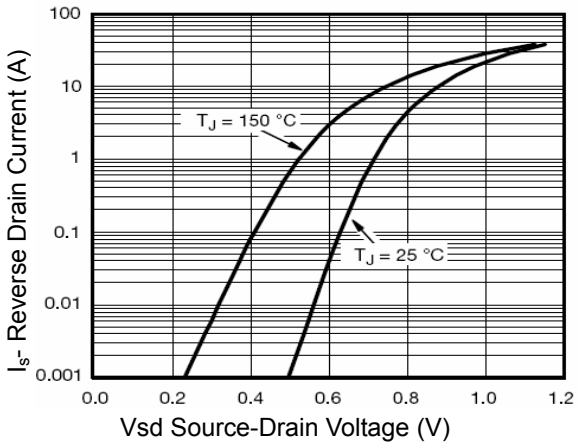


Figure 6 Source- Drain Diode Forward

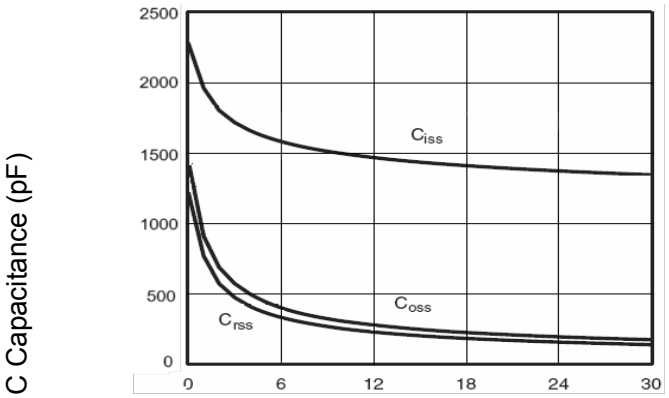


Figure 7 Capacitance vs Vds

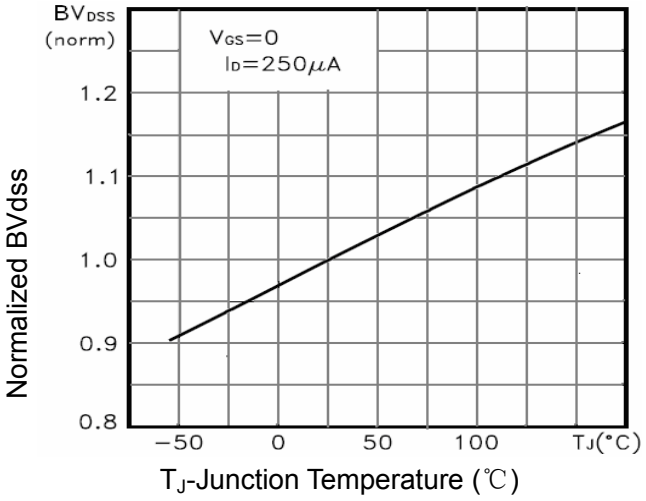


Figure 9 BV_{DSS} vs Junction Temperature

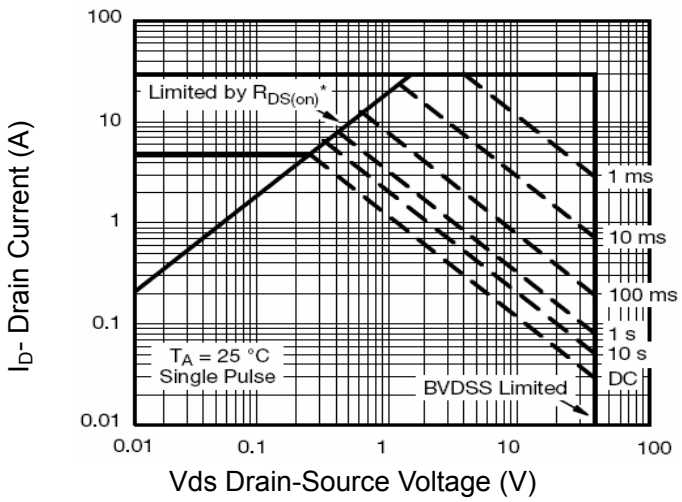


Figure 8 Safe Operation Area

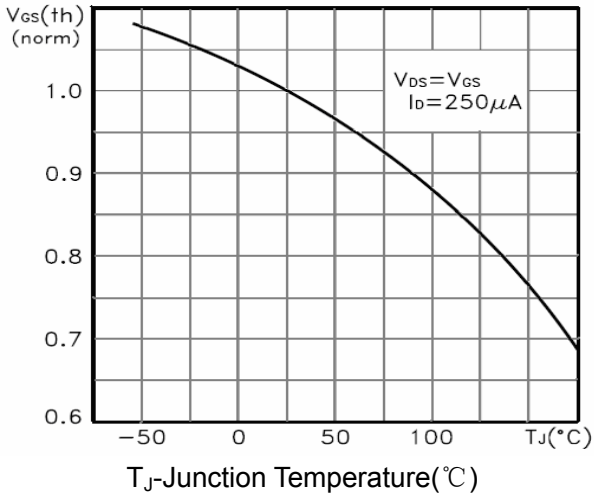


Figure 10 $V_{GS(th)}$ vs Junction Temperature

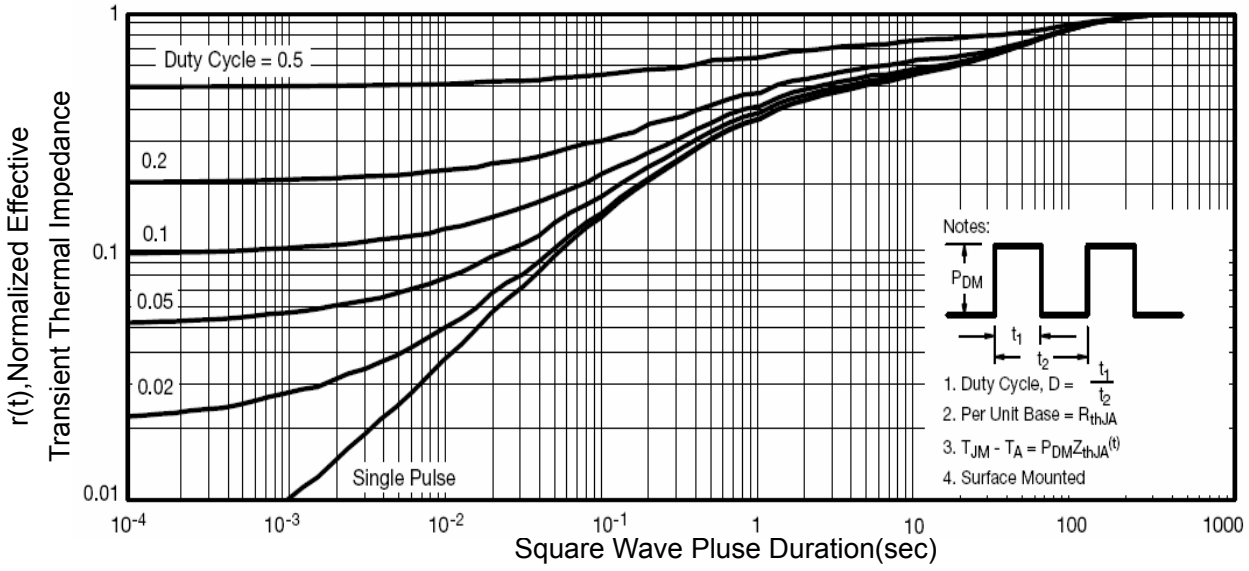
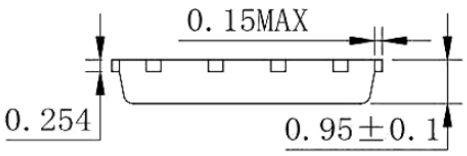
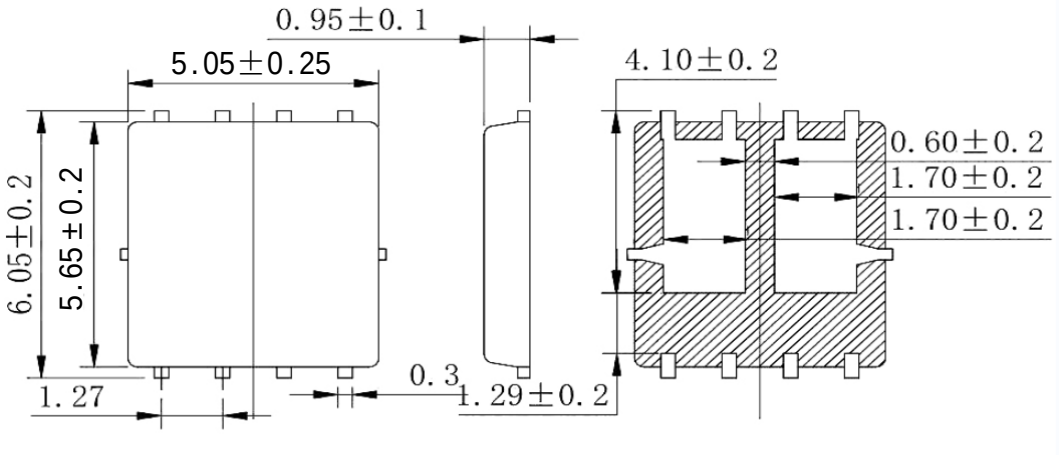


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5×6-8D Package Information：

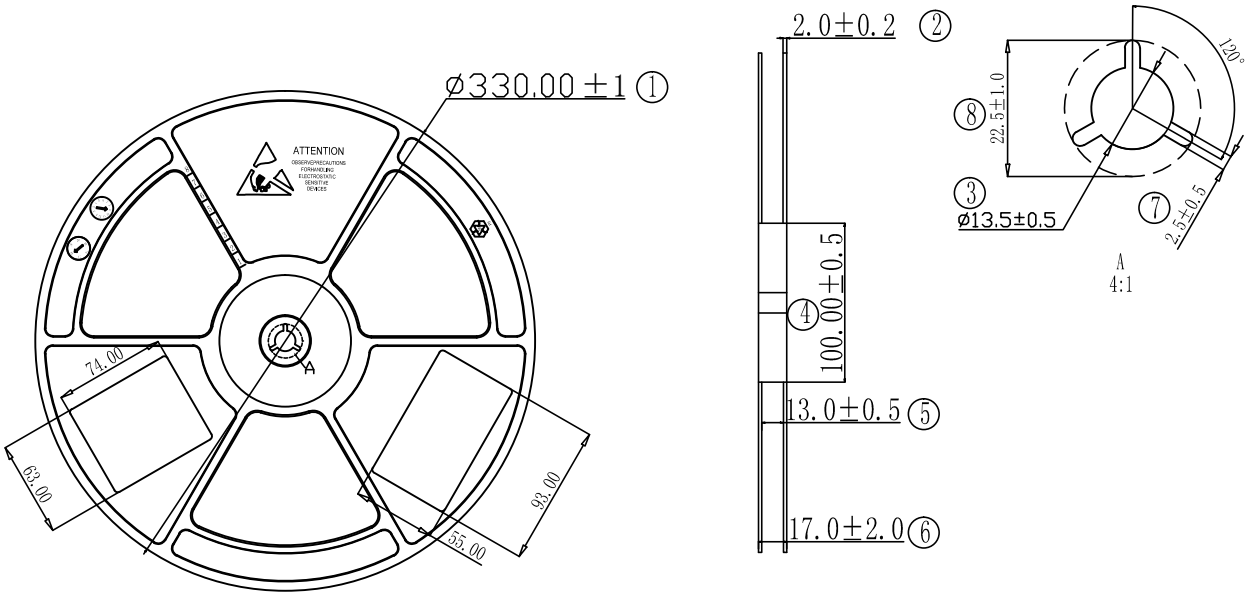


UNIT：mm

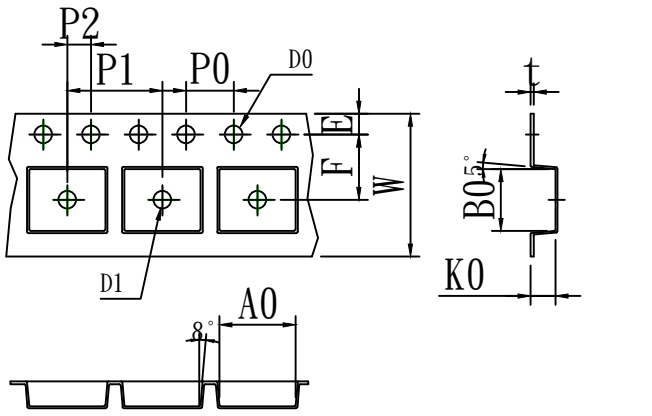


Tape & Reel Information

Dimensions in mm



Symbol	A0	B0	K0	D0	D1	P0	P1	10*P0
Spec	6.15±0.10	5.40±0.10	1.30±0.10	1.55±0.10	1.55±0.10	4.00±0.10	8.00±0.10	40.00±0.10
Symbol	W	E	F	P2	t			
Spec	12.00±0.10	1.75±0.10	5.50±0.10	2.00±0.10	0.20±0.05			



Pulling direction

Marking Information：

①. Doingter LOGO

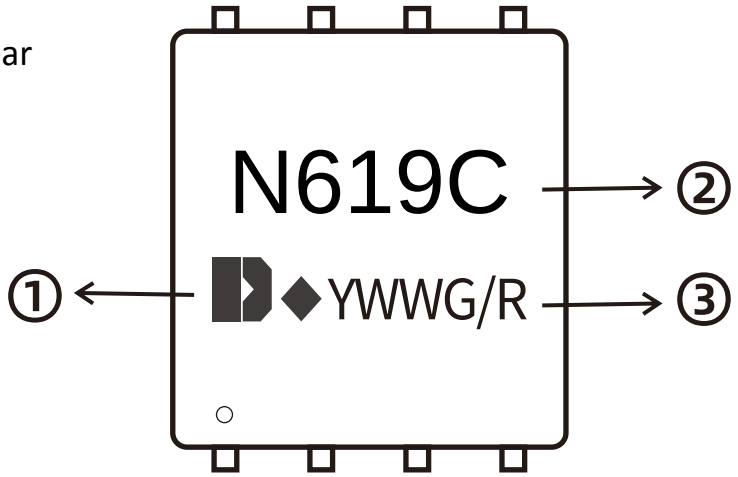
②. Part NO.

③. Date Code(YWWG / R)

Y：Year Code，last digit of the year

WW：Week Code(01-53)

G/R：G(Green) /R(Lead Free)



Previous Version

Version	Date	Subjects (major changes since last revision)
1.0	2025-11-23	Release of final version

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